

# 6N135/6N136

## General Purpose Type Photocoupler T-41-83

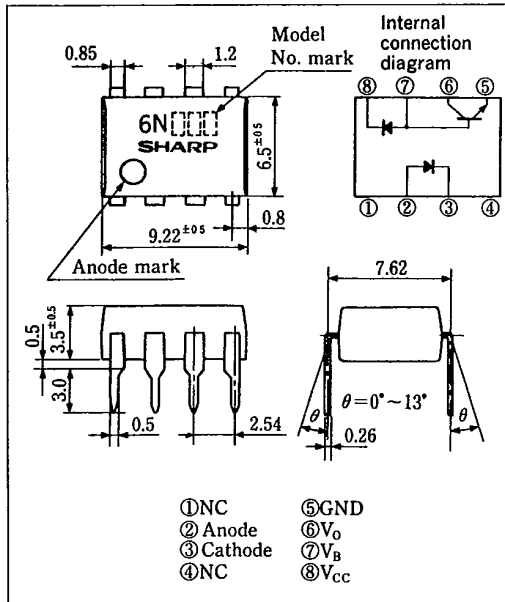
### Features

1. High speed response  $t_{PHL}$ ,  $t_{PLH}$   
(6N135: MAX.  $1.5\mu s$  at  $R_L=4.1k\Omega$ )  
(6N136: MAX.  $0.8\mu s$  at  $R_L=1.9k\Omega$ )
2. High common mode rejection voltage  
( $CM_H$ : TYP.  $1kV/\mu s$ )
3. Standard dual-in-line package
4. UL recognized, file No. E64380

### Applications

1. Computers, measuring instruments, control equipment
2. High speed line receivers, high speed logic
3. Telephone sets
4. Signal transmission between circuits of different potentials and impedances

### Outline Dimensions (Unit : mm)



※OPIC is a registered trademark of Sharp and stands for Optical IC. It has a light detecting element and signal processing circuitry integrated onto a single chip.

### Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Forward current	$I_F$	25	mA
*1 Peak forward current	$I_F$	50	mA
*2 Peak transient forward current	$I_{FM}$	1	A
Reverse voltage	$V_R$	5	V
Power dissipation	P	45	mW
Supply voltage	$V_{CC}$	-0.5 ~ +15	V
Output voltage	$V_O$	-0.5 ~ +15	V
Emitter-base reverse withstand voltage (Pin 5~7)	$V_{EBO}$	5	V
Average output current	$I_O$	8	mA
Peak output current	$I_{OP}$	16	mA
Base current (Pin 7)	$I_B$	5	mA
Power dissipation	$P_O$	100	mW
*3 Isolation voltage	$V_{ISO}$	2,500	V <sub>rms</sub>
Operating temperature	$T_{opr}$	-55 ~ +100	°C
Storage temperature	$T_{stg}$	-55 ~ +125	°C
*4 Soldering temperature	$T_{sol}$	260	°C

\*1 50% duty cycle, Pulse width = 1ms  
Decreases at the rate of 1.6mA/°C if the external temperature is 70°C or more.  
\*2 Pulse width  $\leq 1\mu s$ , 300p/s  
\*3 RH = 40~60%, AC for 1 minute  
\*4 For 10 seconds

## SHARP ELEK/ MELEC DIV

## ■ Electro-optical Characteristics

(T<sub>a</sub>=0~70°C unless otherwise specified)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
*Current transfer ratio	6N135	CTR(1) T <sub>a</sub> =25°C, I <sub>F</sub> =16mA	7.0	40	—	%
	6N136	CTR(1) V <sub>o</sub> =0.4V, V <sub>cc</sub> =4.5V	19	40	—	%
	6N135	CTR(2) I <sub>F</sub> =16mA, V <sub>o</sub> =0.5V	5.0	43	—	%
	6N136	CTR(2) V <sub>cc</sub> =4.5V	15	43	—	%
Logic (0) output voltage	V <sub>OL</sub>	*7 I <sub>F</sub> =16mA, V <sub>cc</sub> =4.5V	—	0.1	0.4	V
Logic (1) output current	I <sub>OH</sub> (1)	T <sub>a</sub> =25°C, I <sub>F</sub> =0 V <sub>cc</sub> =V <sub>o</sub> =5.5V	—	3.0	500	nA
	I <sub>OH</sub> (2)	T <sub>a</sub> =25°C, I <sub>F</sub> =0 V <sub>cc</sub> =V <sub>o</sub> =15V	—	0.01	1.0	μA
	I <sub>OH</sub> (3)	I <sub>F</sub> =0, V <sub>cc</sub> =V <sub>o</sub> =15V	—	—	50	μA
Logic (0) supply current	I <sub>ccL</sub>	I <sub>F</sub> =16mA, V <sub>cc</sub> =15V V <sub>o</sub> =open	—	200	—	μA
Logic (1) supply current	I <sub>ccH</sub> (1)	T <sub>a</sub> =25°C, V <sub>cc</sub> =15V V <sub>o</sub> =open, I <sub>F</sub> =0	—	0.02	1.0	μA
	I <sub>ccH</sub> (2)	V <sub>cc</sub> =15V V <sub>o</sub> =open, I <sub>F</sub> =0	—	—	2.0	μA
Input forward voltage	V <sub>F</sub>	T <sub>a</sub> =25°C, I <sub>F</sub> =16mA	—	1.7	1.95	V
Input forward voltage temperature coefficient	ΔV <sub>F</sub> /ΔT <sub>a</sub>	I <sub>F</sub> =16mA	—	-1.9	—	mV/°C
Input reverse voltage	BV <sub>R</sub>	T <sub>a</sub> =25°C, I <sub>R</sub> =10μA	5.0	—	—	V
Input capacitance	C <sub>IN</sub>	V <sub>F</sub> =0, f=1MHz	—	60	—	PF
*6 Leak current (input-output)	I <sub>I-o</sub>	T <sub>a</sub> =25°C, RH=45%, t=5s V <sub>I-o</sub> =3kVDC	—	—	1.0	μA
*8 Isolation resistance (input-output)	R <sub>I-o</sub>	V <sub>I-o</sub> =500VDC	—	10 <sup>12</sup>	—	Ω
*6 Capacitance (input-output)	C <sub>I-o</sub>	f=1MHz	—	0.6	—	PF
Transistor current amplification factor	h <sub>FE</sub>	V <sub>o</sub> =5V, I <sub>o</sub> =3mA	—	70	—	

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\*5 Current transfer ratio is the ratio of input current and output current expressed in %.

Note) Typical value : at T<sub>a</sub>=25°C

\*6 Measured as 2-pin element (Short 1,2,3,4 and 5,6,7,8)

\*7 6N135 : I<sub>o</sub>=1.1mA, 6N136 : I<sub>o</sub>=2.4mA

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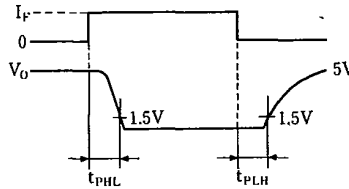
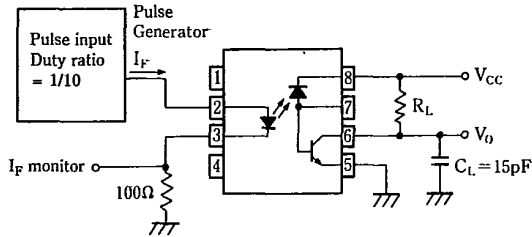
(Ta=25°C, V<sub>CC</sub>=5V, I<sub>F</sub>=16mA)

■ Switching Characteristics

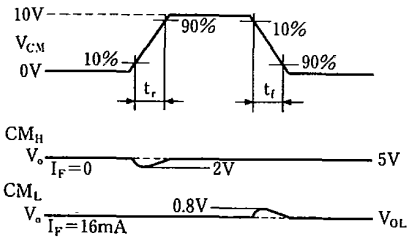
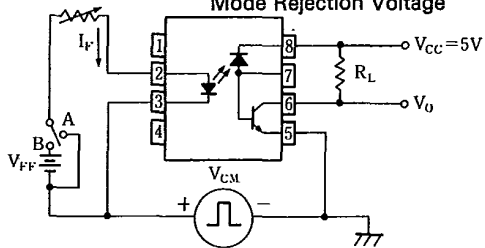
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
**9 Propagation delay time Output (1)→(0)	6N135 t <sub>PHL</sub>	R <sub>L</sub> =4.1kΩ	—	0.3	1.5	μs
	6N136 t <sub>PHL</sub>	R <sub>L</sub> =1.9kΩ	—	0.3	0.8	μs
**9 Propagation delay time Output (0)→(1)	6N135 t <sub>PLH</sub>	R <sub>L</sub> =4.1kΩ	—	0.4	1.5	μs
	6N136 t <sub>PLH</sub>	R <sub>L</sub> =1.9kΩ	—	0.3	0.8	μs
**10,11 Instantaneous common mode rejection voltage "output (1)"	CM <sub>H</sub>	**12 I <sub>F</sub> =0, V <sub>CM</sub> =10V <sub>P-P</sub>	—	1000	—	V/μs
**10,11 Instantaneous common mode rejection voltage "output (0)"	CM <sub>L</sub>	**12 V <sub>CM</sub> =10V <sub>P-P</sub> , I <sub>F</sub> =16mA	—	-1000	—	V/μs
**13 Bandwidth	BW	R <sub>L</sub> =100Ω	—	2.0	—	MHz

- \* 8 R<sub>L</sub>=4.1kΩ is equivalent to one LSTTL and 6.1kΩ pull-up resistor.
- \* 10 Instantaneous common mode rejection voltage "output (1)" represents a common mode voltage variation that can hold the output above (1) level (V<sub>o</sub>>2.0V). Instantaneous common mode rejection voltage "output (0)" represents a common mode voltage variation that can hold the output above (0) level (V<sub>o</sub><0.8V).
- \* 12 6N135 : R<sub>L</sub>=4.1kΩ 6N136 : R<sub>L</sub>=1.9kΩ
- \* 13 Bandwidth represents a point where AC input goes down by 3dB.

\* 9 Test Circuit for Propagation Delay Time



\* 11 Test Circuit for Instantaneous Common Mode Rejection Voltage



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Fig. 1 Forward Current vs. Ambient Temperature

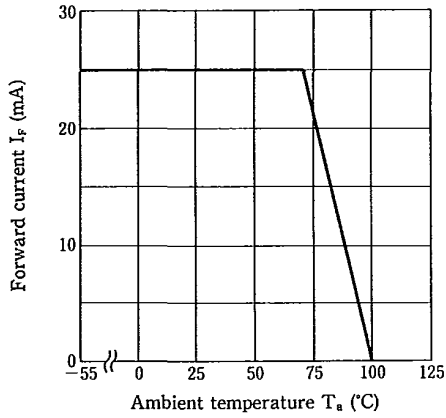


Fig. 2 Power Dissipation vs. Ambient Temperature

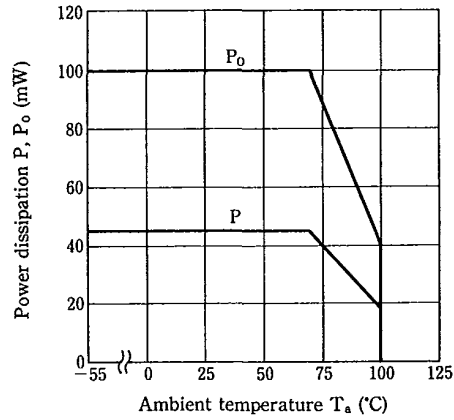


Fig. 3 Forward Current vs. Forward Voltage

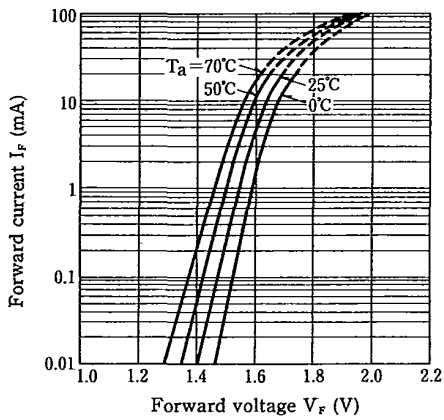
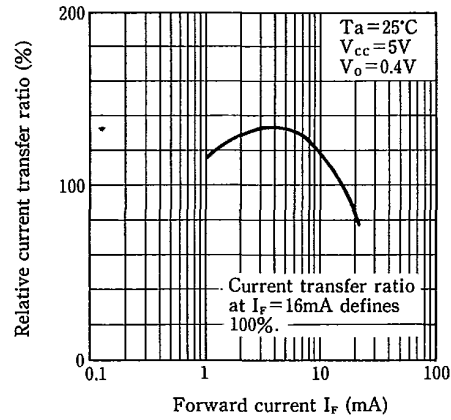
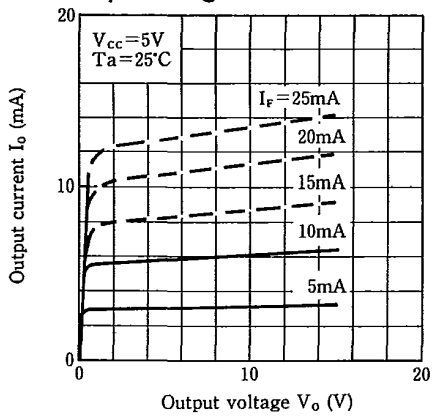


Fig. 4 Relative Current Transfer Ratio vs. Forward Current



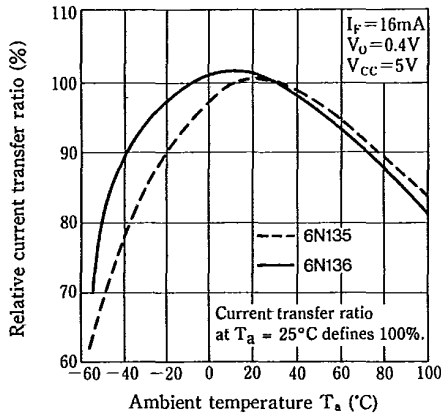
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Fig. 5 Output Current vs. Output Voltage

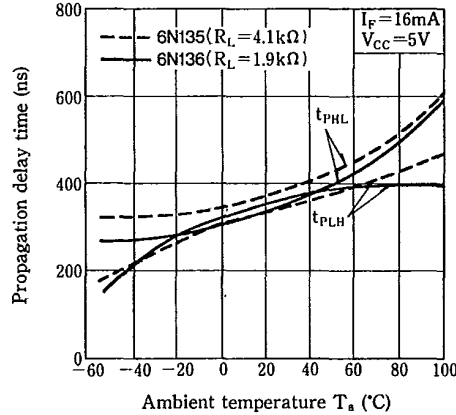


Dotted line : driven by pulse current

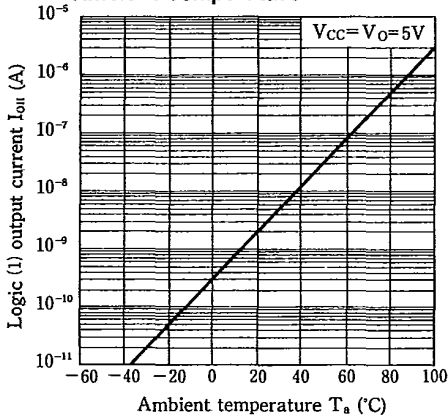
**Fig. 6 Relative Current Transfer Ratio vs. Ambient Temperature**



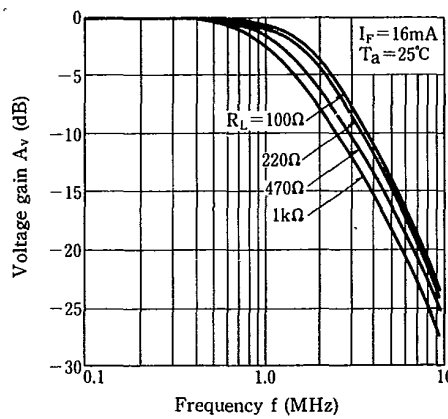
**Fig. 7 Propagation Delay Time vs. Ambient Temperature**



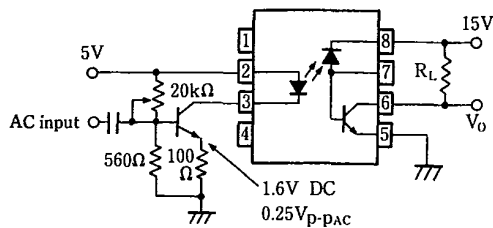
**Fig. 8 Logic (1) Output Current vs. Ambient Temperature**



**Fig. 9 Frequency Response**



**Test Circuit for Frequency Response**



**■ Precaution for Use**

The minute design makes the transistor on the bipolar structured detector vulnerable to static electricity.

To prevent damages and degradation in characteristics due to static electricity, take general measures against static electricity.